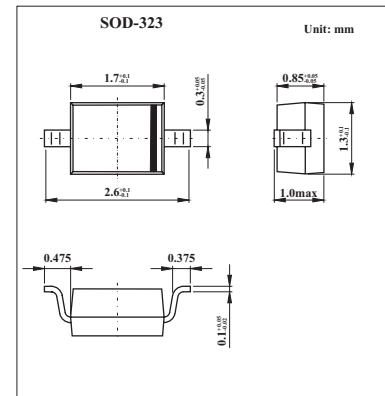


## Silicon Epitaxial Planar Diode

## 1SV313

## ■ Features

- High Capacitance Ratio:  $C_{0.5V}/C_{0.25V}=2.1$  (Typ.)
- Low Series Resistance:  $r_s=0.35\ \Omega$  (Typ.)
- Useful for Small Size Tuner

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	10	V
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	$V_R$	$I_R = 1\ \mu\text{A}$	10			V
Reverse Current	$I_R$	$V_R = 10\ \text{V}$			3	nA
Capacitance	$C_{0.5V}$	$f = 1\ \text{MHz}; V_R = 0.5\ \text{V}$	7.3		8.4	pF
	$C_{0.25V}$	$f = 1\ \text{MHz}; V_R = 0.25\ \text{V}$	2.75		3.4	
Capacitance Ratio	$C_{0.5V}/C_{0.25V}$		2.4	2.5		
Series Resistance	$r_s$	$V_R = 1\ \text{V}, f = 470\ \text{MHz}$		0.35		$\Omega$

## ■ Marking

Marking	V6
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